

Saheb Biwi Aur Gangster 1080p

saheb biwi aur gangster full hd hdw saheb biwi aur gangster 720p saheb biwi aur gangster 3gp1. Field of the Invention The present invention relates to a method for fabricating an inductor, and more particularly, to a method for fabricating an inductor having a complicated shape using a plating process. 2. Description of the Related Art A fabricating method for a semiconductor device such as a metal oxide semiconductor (MOS) transistor and a capacitor, etc. involves the use of the plating process. However, in order to use the plating process, a process for forming a contact hole or an inter-level dielectric layer is required to be performed. Thus, a specific shape of a metal layer is difficult to be formed. In order to form a complicated shape of the inductor, the plating process is used to form a conductive layer on a portion of the complicated shape, and then a portion of the conductive layer is removed, thereby obtaining the complicated shape. The conventional plating process will be described with reference to the attached drawings. FIG. 1 is a cross-sectional view illustrating a plating process. Referring to FIG. 1, a silicon substrate 10 and a metal layer 20 are prepared. The metal layer 20 is formed on a surface of the silicon substrate 10 to a predetermined thickness. A photoresist pattern 30 is then formed on the metal layer 20. Next, the photoresist pattern 30 is etched in a self-aligned manner using the metal layer 20 as a mask to form a hole. Subsequently, the metal layer 20 is etched to expose the silicon substrate 10 in the hole formed by the etching. Thereafter, a contact hole 40 is formed by removing the silicon substrate 10 using the metal layer 20 as a mask. Afterward, the metal layer 20 and the metal layer 20 that is etched are removed. A resultant metal layer 50 includes an upper portion of the metal layer 20 that is formed to have a complicated shape and the contact hole 40. However, as shown in FIG. 1, an exposed portion of the metal layer 20 is a thin and narrow portion. Thus, the exposed portion of the metal layer 20 may be oxidized or delaminated, and the metal layer 20 may be separated from the silicon substrate 10. In order to solve such a problem, a vacuum deposition process may be



